T-46-13-29

Am27C040

4 Megabit (524,288 x 8-Bit) CMOS EPROM

Advanced Micro Devices

DISTINCTIVE CHARACTERISTICS

- **Fast access time**
  - 90 ns
- **Low power consumption**
  - 20 µA typical CMOS standby current
- **JEDEC-approved pinout**
  - plug in upgrade of 1 Megabit and 2 Megabit EPROMs
  - easy upgrade from 28-pin JEDEC EPROMs
- **Single + 5 V power supply**
- **± 10% power supply tolerance standard on most speeds**
- **100% Flashrite™ programming**
  - typical programming time of less than 3 minutes
- **Latch-up protected to 100 mA from –1 V to V_{CC} + 1 V**
- **High noise immunity**
- **Compact 32-pin DIP, PDIP, LCC and PLCC packages require no hardware change for upgrades to 8 megabits**
- **Versatile features for simple interfacing**
  - both CMOS and TTL input/output compatibility
  - two line control functions

GENERAL DESCRIPTION

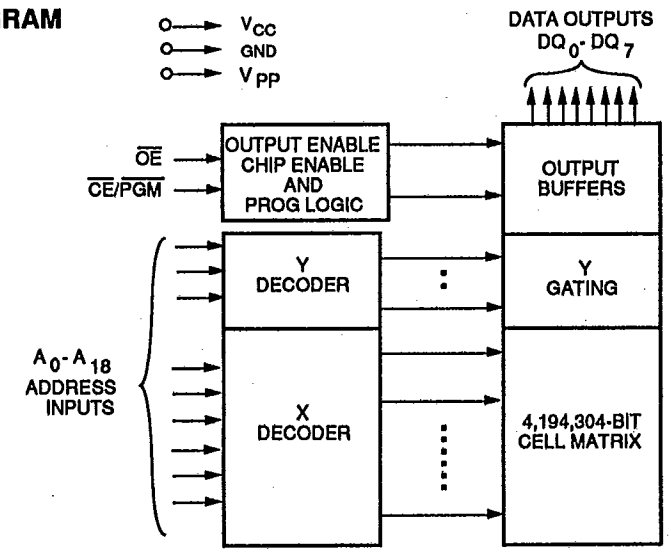
The Am27C040 is a 4 megabit ultraviolet erasable programmable read-only memory. It is organized as 512K words by 8 bits per word, operates from a single + 5 V supply, has a static standby mode, and features fast single address location programming. Products are available in windowed ceramic DIP and LCC packages as well as plastic one time programmable (OTP) PDIP and PLCC packages.

Typically, any byte can be accessed in less than 90 ns, allowing operation with high-performance microprocessors without any WAIT states. The Am27C040 offers separate Output Enable ($\overline{OE}$) and Chip Enable ($\overline{CE}$) controls, thus eliminating bus contention in a multiple bus microprocessor system.

AMD's CMOS process technology provides high speed, low power, and high noise immunity. Typical power consumption is only 100 mW in active mode, and 100 µW in standby mode.

All signals are TTL levels, including programming signals. Bit locations may be programmed singly, in blocks, or at random. The Am27C040 supports AMD's Flashrite™ programming algorithm (100 µs pulses) resulting in typical programming times of less than 3 minutes.

BLOCK DIAGRAM



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PRODUCT SELECTOR GUIDE

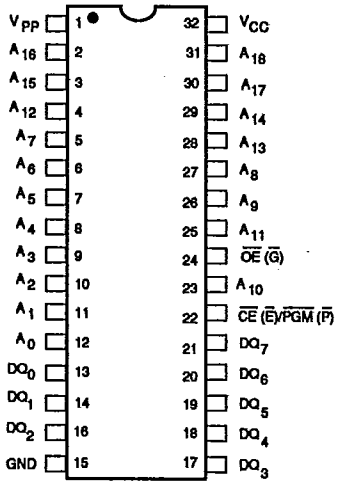
T-46-13-29

Family Part No.	Am27C040				
Ordering Part Number					
V_{CC} ± 5%	-95	-125	-155		-255
V_{CC} ± 10%	-90	-120	-150	-200	-250
Max. Access Time (ns)	90	120	150	200	250
$\overline{CE}$ ($\overline{E}$) Access Time (ns)	90	120	150	200	250
$\overline{OE}$ ($\overline{G}$) Access Time (ns)	40	50	65	75	100

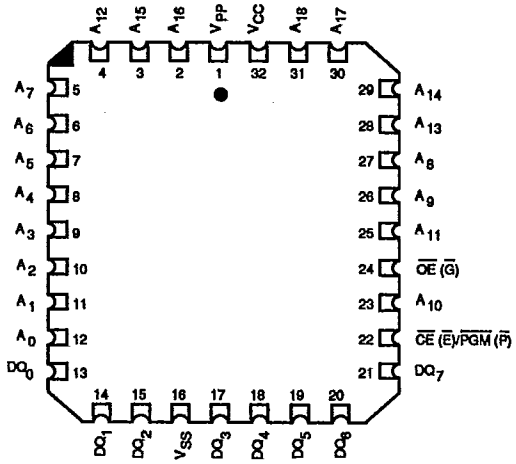
CONNECTION DIAGRAMS

Top View

DIP



LCC*



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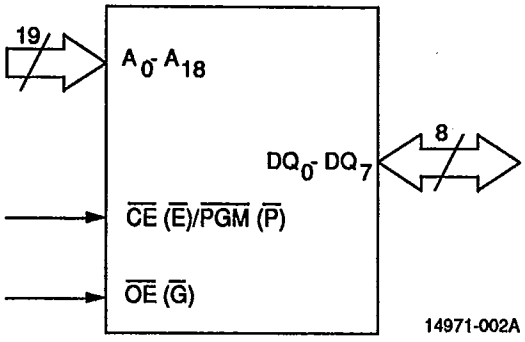
Notes:

1. JEDEC nomenclature is in parentheses.
2. The 32-Pin DIP to 32-Pin LCC configuration varies from the JEDEC 28-Pin DIP to 32-Pin LCC configuration.

* Also available in 32-pin rectangular plastic leaded chip carrier.

LOGIC SYMBOL



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PIN DESCRIPTION

A_0– A_{18}	= Address Inputs
$\overline{CE}$ ($\overline{E}$)/$\overline{PGM}$ ($\overline{P}$)	= Chip and Program Enable Input
DQ_0– DQ_7	= Data Inputs/Outputs
$\overline{OE}$ ($\overline{G}$)	= Output Enable Input
V_{CC}	= V_{CC} Supply Voltage
V_{PP}	= Program Supply Voltage
GND	= Ground

ORDERING INFORMATION

T-46-13-29

EPROM Products

AMD Standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of:

a. **Device Number**
b. **Speed Option**
c. **Package Type**
d. **Temperature Range**
e. **Optional Processing**

AM27C040 -90 D C B

e. OPTIONAL PROCESSING
Blank = Standard processing
B = Burn-In

d. TEMPERATURE RANGE
C = Commercial (0° to +70°C)
I = Industrial (–40° to +85°C)
E = Extended Commercial (–55° to +125°C)

c. PACKAGE TYPE
D = 32-Pin Ceramic DIP (CDV032)
L = 32-Pin Rectangular Ceramic Leadless Chip Carrier (CLV032, JEDEC Type)

b. SPEED OPTION
See Product Selector Guide and Valid Combinations

a. DEVICE NUMBER
Am27C040
4 Megabit (512K x 8) CMOS UV EPROM

Valid Combinations	
AM27C040-90	DC, DCB, LC, LCB
AM27C040-95	
AM27C040-120	DC, DCB, DI, DIB, LC, LCB, LI, LIB
AM27C040-125	
AM27C040-150	DC, DCB, DE, DEB, DI, DIB, LC, LCB, LI, LIB, LE, LEB
AM27C040-200	
AM27C040-255	

Valid Combinations

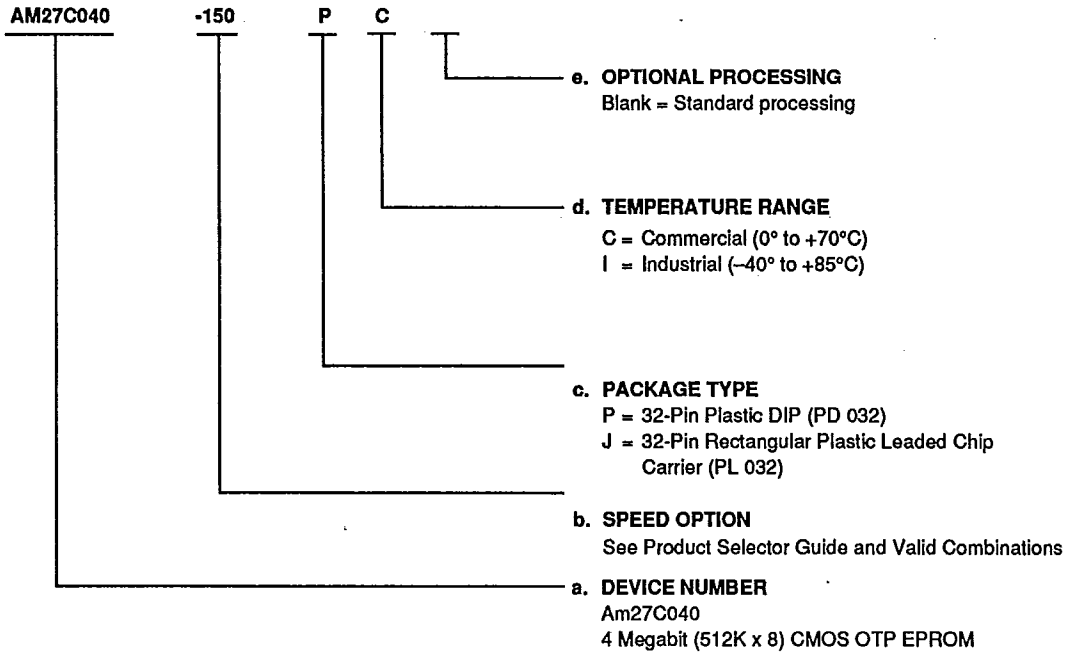
Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations or to check on newly-released combinations.

ORDERING INFORMATION
OTP Products

T-46-13-29

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of:

a. **Device Number**
b. **Speed Option**
c. **Package Type**
d. **Temperature Range**
e. **Optional Processing**



Valid Combinations	
AM27C040-150	PC, JC, PI, JI
AM27C040-155	
AM27C040-200	
AM27C040-250	

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations or to check on newly-released combinations.

ORDERING INFORMATION
Military APL Products

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AMD products for Aerospace and Defense applications are available in several packages and operating ranges. APL (Approved Products List) products are fully compliant with MIL-STD-883C requirements. The order number (Valid Combination) is formed by a combination of:

a. **Device Number**
b. **Speed Option**
c. **Device Class**
d. **Package Type**
e. **Lead Finish**

AM27C040 -150 /B X A

e. **LEAD FINISH**
A = Hot Solder Dip

d. **PACKAGE TYPE**
X = 32-Pin Ceramic DIP (CDV032)
U = 32-Pin Rectangular Ceramic Leadless Chip Carrier (CLV032)

c. **DEVICE CLASS**
/B = Class B

b. **SPEED OPTION**
See Product Selector Guide and Valid Combinations

a. **DEVICE NUMBER**
Am27C040
4 Megabit (512K x 8) CMOS UV EPROM

Valid Combinations	
AM27C040-150	/BXA, /BUA
AM27C040-200	
AM27C040-250	

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations, to check on newly-released combinations.

Group A Tests

Group A tests consist of Subgroups 1,2,3,7,8,9,10,11.

For other Surface Mount Package options, contact NVD Military Marketing.

FUNCTIONAL DESCRIPTION

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Erasing the Am27C040

In order to clear all locations of their programmed contents, it is necessary to expose the Am27C040 to an ultraviolet light source. A dosage of 15 W seconds/cm² is required to completely erase an Am27C040. This dosage can be obtained by exposure to an ultraviolet lamp —wavelength of 2537 Angstroms (Å) —with intensity of 12,000 µW/cm² for 15 to 20 minutes. The Am27C040 should be directly under and about one inch from the source and all filters should be removed from the UV light source prior to erasure.

It is important to note that the Am27C040 and similar devices will erase with light sources having wavelengths shorter than 4000 Å. Although erasure times will be much longer than with UV sources at 2537 Å, exposure to fluorescent light and sunlight will eventually erase the Am27C040 and exposure to them should be prevented to realize maximum system reliability. If used in such an environment, the package window should be covered by an opaque label or substance.

Programming the Am27C040

Upon delivery or after each erasure the Am27C040 has all 4,194,304 bits in the "ONE" or HIGH state. "ZEROs" are loaded into the Am27C040 through the procedure of programming.

The programming mode is entered when 12.75 ± 0.25 V is applied to the V_{PP} pin, $\overline{CE}$ is at V_{IL}, and $\overline{OE}$ is at V_{IH}.

For programming, the data to be programmed is applied 8 bits in parallel to the data output pins.

The flowchart (Figure 2) shows AMD's Flashrite algorithm. The Flashrite algorithm reduces programming time by using 100 µs programming pulses and by giving each address only as many pulses as is necessary in order to reliably program the data. After each pulse is applied to a given address, the data in that address is verified. If the data does not verify, additional pulses are given until it verifies or the maximum is reached. This process is repeated while sequencing through each address of the Am27C040. This part of the algorithm is done at V_{CC} = 6.25 V to assure that each EPROM bit is programmed to a sufficiently high threshold voltage. After the final address is completed, the entire EPROM memory is verified at $V_{CC} = V_{PP}$ = 5.25 V.

Program Inhibit

Programming of multiple Am27C040 in parallel with different data is also easily accomplished. Except for $\overline{CE}$, all like inputs of the parallel Am27C040 may be common. A TTL low-level program pulse applied to an Am27C040 $\overline{CE}$ input with V_{PP} = 12.75 ± 0.25 V, and $\overline{OE}$ HIGH will program that Am27C040. A high-level $\overline{CE}$ input inhibits the other Am27C040 devices from being programmed.

Program Verify

A verify should be performed on the programmed bits to determine that they were correctly programmed. The verify should be performed with $\overline{OE}$ at V_{IL}, $\overline{CE}$ at V_{IH} and V_{PP} between 12.5 V and 13.0 V.

Auto Select Mode

The auto select mode allows the reading out of a binary code from an EPROM that will identify its manufacturer and type. This mode is intended for use by programming equipment for the purpose of automatically matching the device to be programmed with its corresponding programming algorithm. This mode is functional in the 25°C ± 5°C ambient temperature range that is required when programming the Am27C040.

To activate this mode, the programming equipment must force 12.0 ± 0.5 V on address line A_9 of the Am27C040. Two identifier bytes may then be sequenced from the device outputs by toggling address line A_0 from V_{IL} to V_{IH}. All other address lines must be held at V_{IL} during auto select mode.

Byte 0 ($A_0 = V_{IL}$) represents the manufacturer code, and byte 1 ($A_0 = V_{IH}$), the device identifier code. For the Am27C040, these two identifier bytes are given in the Mode Select Table. All identifiers for manufacturer and device codes will possess odd parity, with the MSB (DQ_7) defined as the parity bit.

Read Mode

The Am27C040 has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip Enable ($\overline{CE}$) is the power control and should be used for device selection. Output Enable ($\overline{OE}$) is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that addresses are stable, address access time (t_{ACC}) is equal to the delay from $\overline{CE}$ to output (t_{CE}). Data is available at the outputs t_{OE} after the falling edge of $\overline{OE}$, assuming that $\overline{CE}$ has been LOW and addresses have been stable for at least $t_{ACC} - t_{OE}$.

Standby Mode

The Am27C040 has a CMOS standby mode which reduces the maximum V_{CC} current to 100 µA. It is placed in CMOS-standby when $\overline{CE}$ is at V_{CC} ± 0.3 V. The Am27C040 also has a TTL-standby mode which reduces the maximum V_{CC} current to 1.0 mA. It is placed in TTL-standby when $\overline{CE}$ is at V_{IH}. When in standby mode, the outputs are in a high-impedance state, independent of the $\overline{OE}$ input.

Output OR-Tieing

To accommodate multiple memory connections, a two-line control function is provided to allow for:

1. Low memory power dissipation, and
2. Assurance that output bus contention will not occur.

It is recommended that $\overline{CE}$ be decoded and used as the primary device-selecting function, while $\overline{OE}$ be made a common connection to all devices in the array and connected to the READ line from the system control bus. This assures that all deselected memory devices are in low-power standby mode and that the output pins are only active when data is desired from a particular memory device.

System Applications

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During the switch between active and standby conditions, transient current peaks are produced on the rising and falling edges of Chip Enable. The magnitude of these transient current peaks is dependent on the output capacitance loading of the device. At a minimum, a 0.1 µF ceramic capacitor (high frequency, low inherent inductance) should be used on each device between V_{CC} and GND to minimize transient effects. In addition, to overcome the voltage drop caused by the inductive effects of the printed circuit board traces on EPROM arrays, a 4.7 µF bulk electrolytic capacitor should be used between V_{CC} and GND for each eight devices. The location of the capacitor should be close to where the power supply is connected to the array.

MODE SELECT TABLE

Mode \ Pins		$\overline{CE}/\overline{PGM}$	$\overline{OE}$	A_0	A_9	V_{PP}	Outputs
Read		V_{IL}	V_{IL}	X	X	X	D_{OUT}
Output Disable		V_{IL}	V_{IH}	X	X	X	Hi-Z
Standby (TTL)		V_{IH}	X	X	X	X	Hi-Z
Standby (CMOS)		$V_{CC} \pm 0.3$ V	X	X	X	X	Hi-Z
Program		V_{IL}	V_{IH}	X	X	V_{PP}	D_{IN}
Program Verify		V_{IH}	V_{IL}	X	X	V_{PP}	D_{OUT}
Program Inhibit		V_{IH}	V_{IH}	X	X	V_{PP}	Hi-Z
Auto Select (Note 3)	Manufacturer Code	V_{IL}	V_{IL}	V_{IL}	V_H	X	01H
	Device Code	V_{IL}	V_{IL}	V_{IH}	V_H	X	9BH

Notes:

1. $V_H = 12.0 \pm 0.5$ V
2. X = Either V_{IH} or V_{IL}
3. $A_1 - A_8 = A_{10} - A_{18} = V_{IL}$
4. See DC Programming Characteristics for V_{PP} voltage during programming.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature

OTP products	–65° to +125°C
All other products	–65° to +150°C
Ambient Temperature with Power Applied	–55° to +125°C

Voltage with Respect to Ground:

All pins except A_9, V_{PP}, V_{CC} (Note 1)	–0.6 to V_{CC} + 0.6 V
A_9 and V_{PP} (Note 2)	–0.6 to +13.5 V
V_{CC}	–0.6 to +7.0 V

Stresses above those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure of the device to absolute maximum rating conditions for extended periods may affect device reliability.

Notes:

1. During transitions, the inputs may overshoot GND to –2.0 V for periods of up to 20 ns. Maximum DC voltage on input may overshoot to V_{CC} + 2.0 V for periods of up to 20 ns.
2. During transitions, A_9 and V_{PP} may overshoot GND to –2.0 V for periods of up to 20 ns. A_9 and V_{PP} must not exceed 13.5 V for any period of time.

OPERATING RANGES

T-46-13-29

Commercial (C) Devices

Case Temperature (T_C)	0° to +70°C

Industrial (I) Devices

Case Temperature (T_C)	–40° to +85°C

Extended Commercial (E) Devices

Case Temperature (T_C)	–55° to +125°C

Military (M) Devices

Case Temperature (T_C)	–55° to +125°C

Supply Read Voltages:

V_{CC} for Am27C040-XX5	+4.75 to +5.25 V
V_{CC} for Am27C040-XX0	+4.50 to +5.50 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC CHARACTERISTICS over operating range unless otherwise specified. (Notes 1, 4, 5, and 8)

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(for APL Products, Group A, Subgroups 1, 2, 3, 7, and 8 are tested unless otherwise noted)

TTL and NMOS

Parameter Symbol	Parameter Description	Test Conditions		Min.	Max.	Unit
V_{OH}	Output HIGH Voltage	I_{OH} = –400 µA		2.4		V
V_{OL}	Output LOW Voltage	I_{OL} = 2.1 mA			0.45	V
V_{IH}	Input HIGH Voltage			2.0	V_{CC} + 0.5	V
V_{IL}	Input LOW Voltage			–0.5	+0.8	V
I_{LI}	Input Load Current	V_{IN} = 0 V to +V_{CC}	C/I Devices		1.0	µA
			E/M Devices		5.0	
I_{LO}	Output Leakage Current	V_{OUT} = 0 V to +V_{CC}	C/I Devices		5.0	µA
			E/M Devices		10.0	
I_{CC1}	V_{CC} Active Current (Notes 5, 9)	$\overline{CE}$ = V_{IL}, f = 5 MHz, I_{OUT} = 0 mA (Open Outputs)	C/I Devices		40	mA
			E/M Devices		60	
I_{CC2}	V_{CC} Standby Current	$\overline{CE}$ = V_{IH}	C/I Devices		1.0	mA
			E/M Devices		1.0	
I_{PP1}	V_{PP} Current During Read (Note 6)	$\overline{CE}$ = $\overline{OE}$ = V_{IL}, V_{PP} = V_{CC}			100	µA

CMOS

Parameter Symbol	Parameter Description	Test Conditions		Min.	Max.	Unit
V_{OH}	Output HIGH Voltage	I_{OH} = –400 µA		V_{CC} – 0.8 V		V
V_{OL}	Output LOW Voltage	I_{OL} = 2.1 mA			0.45	V
V_{IH}	Input HIGH Voltage			0.7 V_{CC}	V_{CC} + 0.5	V
V_{IL}	Input LOW Voltage			–0.5	+0.8	V
I_{LI}	Input Load Current	V_{IN} = 0 V to +V_{CC}	C/I Devices		1.0	µA
			E/M Devices		5.0	
I_{LO}	Output Leakage Current	V_{OUT} = 0 V to +V_{CC}	C/I Devices		5.0	µA
			E/M Devices		10.0	
I_{CC1}	V_{CC} Active Current (Notes 5, 9)	$\overline{CE}$ = V_{IL}, f = 5 MHz, I_{OUT} = 0 mA (Open Outputs)	C/I Devices		40	mA
			E/M Devices		60	
I_{CC2}	V_{CC} Standby Current	$\overline{CE}$ = V_{CC} ± 0.3 V	C/I Devices		100	µA
			E/M Devices		100	
I_{PP1}	V_{PP} Current During Read (Note 6)	$\overline{CE}$ = $\overline{OE}$ = V_{IL}, V_{PP} = V_{CC}			100	µA

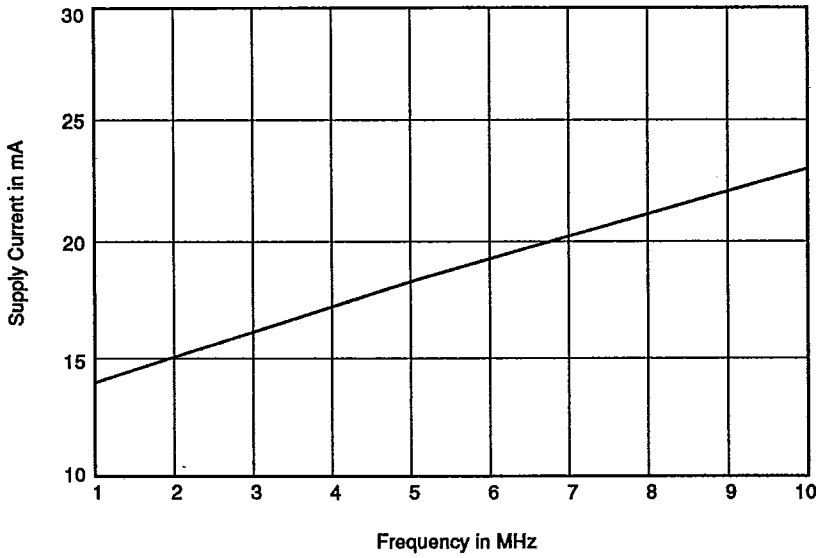

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Figure 1. Typical Supply Current vs. Frequency
V_{CC} = 5.0 V, T = 25°C

CAPACITANCE (Notes 2, 3, and 7)

Parameter Symbol	Parameter Description	Test Conditions	CDV032		CLV032		Unit
			Typ.	Max.	Typ.	Max.	
C_{IN}	Input Capacitance	V_{IN} = 0 V	10	12	8	10	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0 V	12	15	9	12	pF

Notes:

1. V_{CC} must be applied simultaneously or before V_{PP}, and removed simultaneously or after V_{PP}.
2. Typical values are for nominal supply voltages.
3. This parameter is only sampled, not 100% tested.
4. **Caution:** the Am27C040 must not be removed from (or inserted into) a socket when V_{CC} or V_{PP} is applied.
5. I_{CC1} is tested with OE = V_{IH} to simulate open outputs.
6. Maximum active power usage is the sum of I_{CC} and I_{PP}.
7. T_A = +25°C, f = 1 MHz.
8. Minimum DC Input Voltage is -0.5 V. During transitions, the inputs overshoot to -2.0 V for periods less than 20 ns. Maximum DC Voltage on output pins is V_{CC} +0.5 V, which may overshoot to V_{CC} +2.0 V for periods less than 20 ns.
9. For typical supply current values at various frequencies, refer to Figure 1.

SWITCHING CHARACTERISTICS over operating range unless otherwise specified. (Notes 1, 3, and 4)

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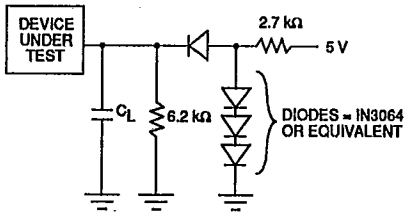
(for APL Products, Group A, Subgroups 9, 10, and 11 are tested unless otherwise noted)

Parameter Symbols		Parameter Description	Test Conditions		Am27C040					Unit
JEDEC	Standard				-90, -95	-120, -125	-150, -155	-200	-255, -250	
t_{AVQV}	t_{ACC}	Address to Output Delay	$\overline{CE} = \overline{OE}_L = V_I$	Min.	–	–	–	–	–	ns
				Max.	90	120	150	200	250	
t_{ELQV}	t_{CE}	Chip Enable to Output Delay	$\overline{OE} = V_{IL}$	Min.	–	–	–	–	–	ns
				Max.	90	120	150	200	250	
t_{GLQV}	t_{OE}	Output Enable to Output Delay	$\overline{CE} = V_{IL}$	Min.	–	–	–	–	–	ns
				Max.	40	50	65	75	100	
t_{EHQZ} t_{GHQZ}	t_{DF} (Note 2)	Chip Enable HIGH or Output Enable HIGH, whichever comes first, to Output Float		Min.	–	0	0	0	0	ns
				Max.	30	40	50	60	60	
t_{AXQX}	t_{OH}	Output Hold from Addresses, $\overline{CE}$, or $\overline{OE}$, whichever occurred first		Min.	0	0	0	0	0	ns
				Max.	–	–	–	–	–	

Notes:

1. V_{CC} must be applied simultaneously or before V_{PP}, and removed simultaneously or after V_{PP}.
2. This parameter is only sampled, not 100% tested.
3. **Caution:** The Am27C040 must not be removed from (or inserted into) a socket or board when V_{pp} or V_{cc} is applied.
4. Output Load: 1 TTL gate and C_L = 100 pF
   Input Rise and Fall Times: 20 ns
   Input Pulse Levels: 0.45 to 2.4 V
   Timing Measurement Reference Level — Inputs: 0.8 to 2.0 V
   Outputs: 0.8 to 2.0 V

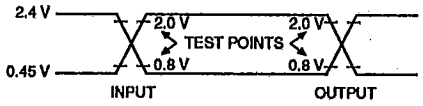
SWITCHING TEST CIRCUIT



C_L = 100 pF including jig capacitance.

10205A-004A

SWITCHING TEST WAVEFORM



AC Testing: Inputs are driven at 2.4 V for a logic "1" and 0.45 V for a logic "0." Input pulse rise and fall times are ≤ 20 ns.

10205B-009A

KEY TO SWITCHING WAVEFORMS

T-46-13-29

WAVEFORM	INPUTS	OUTPUTS
	Must Be Steady	Will Be Steady
	May Change from H to L	Will Be Changing from H to L
	May Change from L to H	Will Be Changing from L to H
	Don't Care Any Change Permitted	Changing State Unknown
	Does Not Apply	Center Line is High Impedance "Off" State

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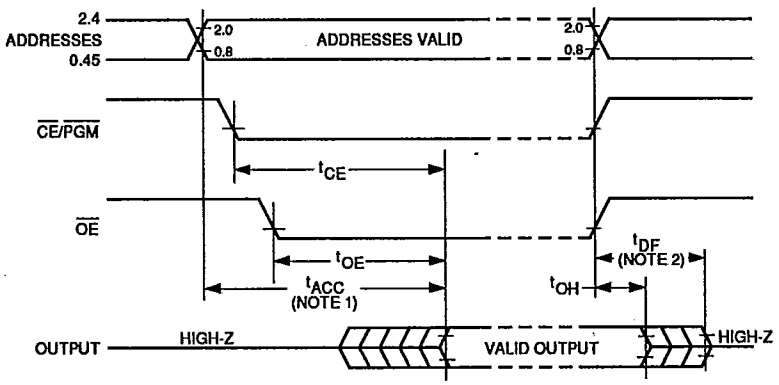
SWITCHING WAVEFORMS



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Notes:

1. $\overline{OE}$ may be delayed up to $t_{ACC} - t_{OE}$ after the falling edge of $\overline{CE}$ without impact on t_{ACC}.
2. t_{DF} is specified from $\overline{OE}$ or $\overline{CE}$, whichever occurs first.

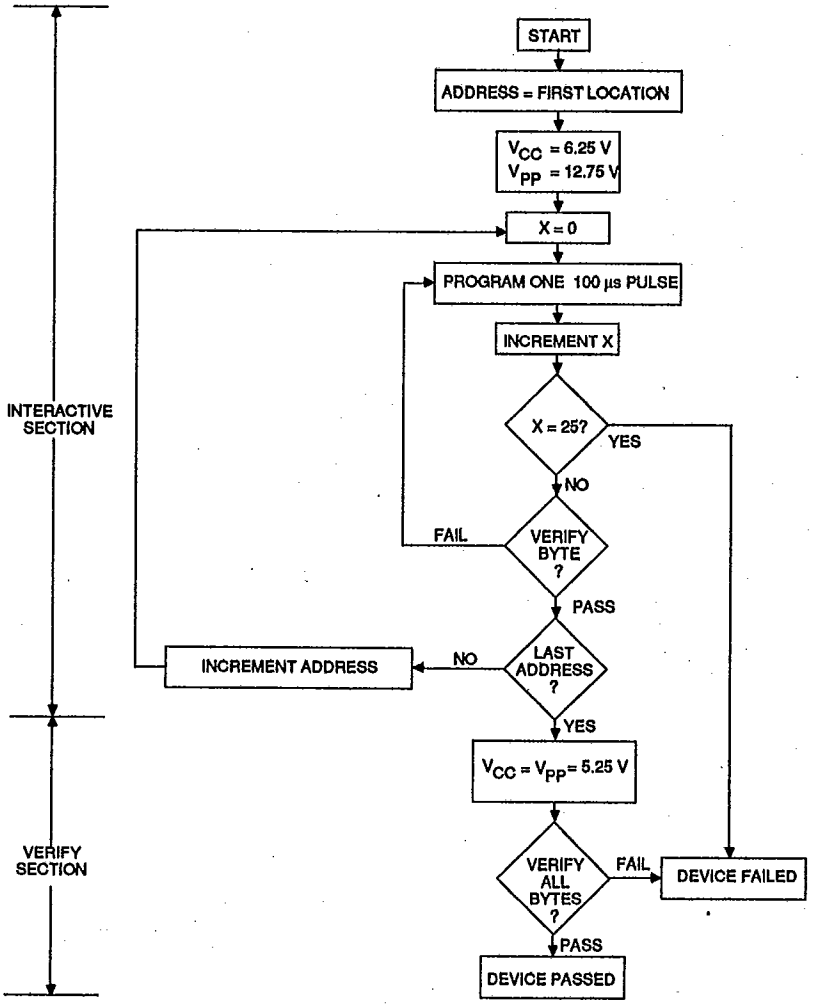

Figure 2. Flashrite Programming Flow Chart

DC PROGRAMMING CHARACTERISTICS (T_A = +25°C ± 5°C) (Notes 1, 2, and 3) T-46-13-29

Parameter Symbol	Parameter Description	Test Conditions	Min.	Max.	Unit
I_{LI}	Input Current (All Inputs)	$V_{IN} = V_{IL}$ or V_{IH}		1.0	µA
V_{IL}	Input LOW Level (All Inputs)		-0.5	0.8	V
V_{IH}	Input HIGH Level		2.0	V_{CC} + 0.5	V
V_{OL}	Output LOW Voltage During Verify	I_{OL} = 2.1 mA		0.45	V
V_{OH}	Output HIGH Voltage During Verify	I_{OH} = -400 µA	2.4		V
V_H	A_9 Auto Select Voltage		11.5	12.5	V
I_{CC}	V_{CC} Supply Current (Program & Verify)			50	mA
I_{PP}	V_{PP} Supply Current (Program)	$\overline{CE} = V_{IL}$, $\overline{OE} = V_{IH}$		30	mA
V_{CC}	Flashrite Supply Voltage		6.00	6.50	V
V_{PP}	Flashrite Programming Voltage		12.5	13.0	V

SWITCHING PROGRAMMING CHARACTERISTICS (T_A = +25°C ± 5°C) (Notes 1, 2, and 3)

Parameter Symbols		Parameter Description	Min.	Max.	Unit
JEDEC	Standard				
t_{AVEL}	t_{AS}	Address Setup Time	2		µs
t_{DZGL}	t_{OES}	$\overline{OE}$ Setup Time	2		µs
t_{DVEL}	t_{DS}	Data Setup Time	2		µs
t_{GHAX}	t_{AH}	Address Hold Time	0		µs
t_{EHDX}	t_{DH}	Data Hold Time	2		µs
t_{GHQZ}	t_{DFP}	Output Enable to Output Float Delay	0	130	ns
t_{VPS}	t_{VPS}	V_{PP} Setup Time	2		µs
t_{ELEH1}	t_{PW}	$\overline{PGM}$ Program Pulse Width	95	105	µs
t_{VCS}	t_{VCS}	V_{CC} Setup Time	2		µs
t_{ELPL}	t_{CES}	$\overline{CE}$ Setup Time	2		µs
t_{GLQV}	t_{OE}	Data Valid from $\overline{OE}$		150	ns

Notes:

1. V_{CC} must be applied simultaneously or before V_{PP}, and removed simultaneously or after V_{PP}.
2. When programming the Am27C040, a 0.1-µF capacitor is required across V_{PP} and ground to suppress spurious voltage transients that may damage the device.
3. Programming characteristics are sampled but not 100% tested at worst-case conditions.

FLASHRITE PROGRAMMING ALGORITHM WAVEFORM (Notes 1 and 2)

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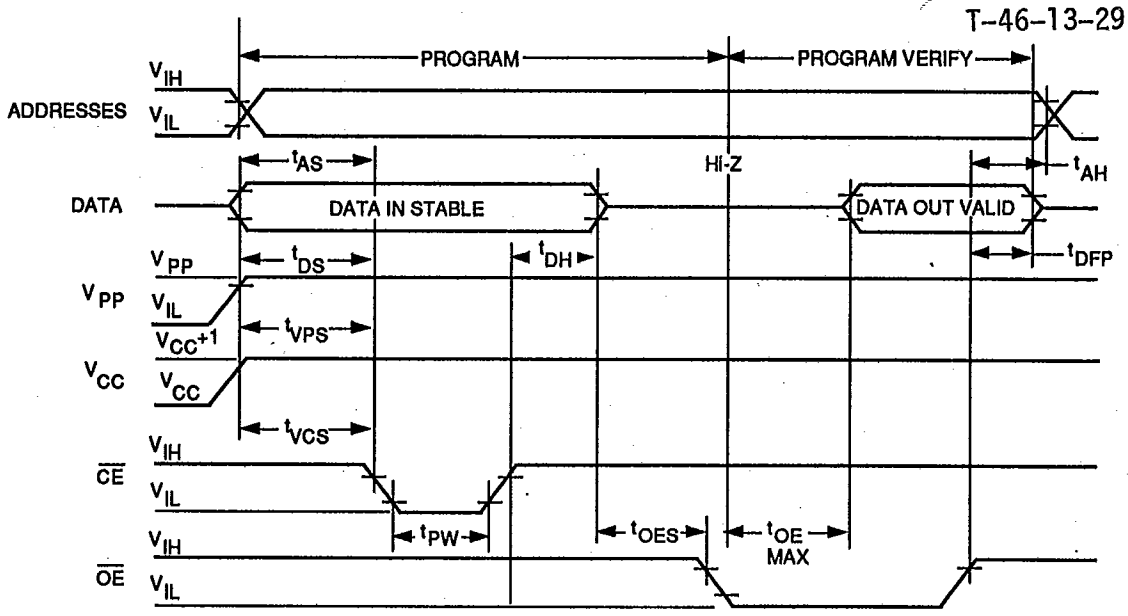

Notes:

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1. The input timing reference level is 0.8 V for a V_{IL} and 2 V for a V_{IH}.
2. t_{OE} and t_{DFP} are characteristics of the device but must be accommodated by the programmer.